

In the claims:

Please substitute the following full listing of claims for the original claim listing.

1 -7 (Cancelled)

1 8. (Original) Method for making a field effect transistor with a current channel with  
2 longitudinal stress, comprising the steps of:

- 3 a) forming an undercut area under the channel; and  
4 b) forming a compressive film in the undercut area so that longitudinal stress is  
5 created in the channel.

1 9. (Original) The method of claim 8 wherein the undercut area is located at an end of  
2 the channel.

1 10. (Original) The method of claim 8 wherein the undercut area is located under a middle  
2 portion of the channel.

1 11. (Original) The method of claim 10 wherein the channel is released in the middle  
2 portion.

1 12. (Original) The method of claim 8 wherein the undercut area is created by etching a  
2 buried oxide layer from under the channel.

1 13. (Original) The method of claim 8 wherein the compressive film is formed by  
2 depositing polysilicon and then oxidizing the polysilicon.

14 - 15 (Cancelled)